

PDF DATA SHEET EFORCEAUSTRALIA PTY.LTD ACN:159 503 401

MDL-III-852L /1~30mW

SPECIFICATIONS

INFRARED DIODE LASER AT 852nm

Infrared diode laser at 852nm is made features of round spot, long lifetime, low cost and easy operating, which is widely used in measurement, spectrum analysis, etc.



Wavelength (nm)	852 ± 10	852 ± 10		
Output power (mW)	>1, 5, 10,, 30	>1, 5, 10,, 30		
Spectral line width (nm)	<0.5	<0.5		
Transverse mode	Near TEM ₀₀	Near TEM ₀₀		
Operating mode	CW	CW		
Power stability (rms, over 4 hours)	<1%, <3%, <5%	<1%, <3%, <5%		
Warm-up time (minutes)	<5	<5		
Beam divergence, full angle (mrad)	<1.0	<1.0		
Dimensions of beam at the aperture (mm)	~3.0	~3.0		
Beam height from base plate (mm)	24.8	24.8		
Operating temperature (°C)	10~35	10~35		
Power supply (90-264VAC)	PSU-III-LED	PSU-III-FDA	PSU-III-OEM	TEAJONER IN WATEROID SEA
Modulation option	TTL/Analog 1Hz-5H	TTL/Analog 1Hz-5KHz, 1Hz-10KHz, 1Hz-30KHz, and TTL on/off		
Expected lifetime (hours)	10000	10000		
Warranty	1 year	1 year		

